

ABSTRACT OF THE DISCLOSURE

The invention includes a semiconductive processing method of electrochemical-mechanical removing at least some of a conductive material from over a surface of a semiconductor substrate. A cathode is provided at a first location of the wafer, and an anode is provided at a second location of the wafer. The conductive material is polished with the polishing pad polishing surface. The polishing occurs at a region of the conductive material and not at another region. The region where the polishing occurs is defined as a polishing operation location. The polishing operation location is displaced across the surface of the substrate from said second location of the substrate toward said first location of the substrate. The polishing operation location is not displaced from said first location toward said second location when the polishing operation location is between the first and second locations. The invention also includes a semiconductor processing method of removing at least some of a conductive material from over a surface of a semiconductive material wafer. A polishing pad is displaced across an upper surface of the wafer from a central region of the wafer toward a periphery of the wafer, and is not displaced from the periphery to the central region.